

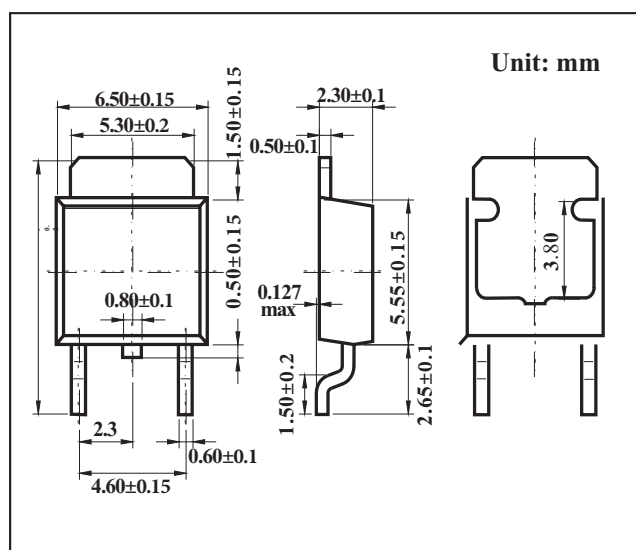
TO-252 Plastic-Encapsulate Transistors

FEATURES

- Low $V_{CE(sat)}$. $V_{CE(sat)} = -0.5V$
- PNP Transistors

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-40	V
Collector - Emitter Voltage	V _{CEO}	-32	
Emitter - Base Voltage	V _{EB0}	-5	
	I _C	-2	A
Collector current -Pulse	I _{CP}	-3	
Collector Power Dissipation T _c =25°C T _a = 25°C	P _C	1.5	W
		1	
Junction Temperature	T _J	150	°C
Storage Temperature rang	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\text{ }\mu\text{A}, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\text{ mA}, I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\text{ }\mu\text{ A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -30\text{V}, I_E = 0$			-1	uA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\text{V}, I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{mA}$		-0.5	-0.8	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -3\text{V}, I_C = -500\text{ mA}$	120		390	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		50		pF
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_E = 500\text{mA}, f = 100\text{MHz}$		100		MHz

RATINGS AND CHARACTERISTIC CURVES

